

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI BLV30** is Designed for Television Band IV & V Applications up to 860 MHz.

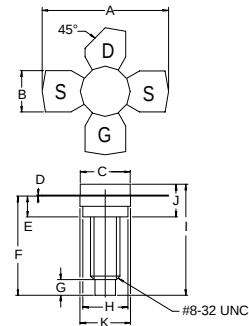
FEATURES:

- Common Emitter
- $P_G = 10$ dB at 2.0 W/860 MHz
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	1.5 A
V_{CBO}	60 V
V_{CEO}	30 V
V_{EBO}	4.0 V
P_{DISS}	15.9 W @ $T_C = 25^\circ\text{C}$
T_J	-65°C to $+200^\circ\text{C}$
T_{STG}	-65°C to $+150^\circ\text{C}$
θ_{JC}	10°C/W

PACKAGE STYLE .280 4L STUD



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	1.010 / 25.65	1.055 / 26.80
B	.220 / 5.59	.230 / 5.84
C	.270 / 6.86	.285 / 7.24
D	.003 / 0.08	.007 / 0.18
E	.117 / 2.97	.137 / 3.48
F	.572 / 14.53	
G	.130 / 3.30	
H	.245 / 6.22	.255 / 6.48
I	.640 / 16.26	
J	.175 / 4.45	.217 / 5.51
K	.275 / 6.99	.285 / 7.24

CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	$I_C = 10$ mA	60			V
BV_{CEO}	$I_C = 50$ mA	30			V
BV_{EBO}	$I_E = 4.0$ mA	4.0			V
I_{CBO}	$V_{CB} = 30$ V			4.0	mA
h_{FE}	$V_{CE} = 25$ V $I_C = 500$ mA	15		120	---
C_{OB}	$V_{CB} = 28$ V $f = 1.0$ MHz			10	pF
P_G IMD_1	$V_{CE} = 25$ V $I_C = 410$ mA $f = 860$ MHz $P_{OUT} = 2.0$ W	10 -60			dB dBc